

N-Channel Trench Power MOSFET

Features

- N-channel
- $V_{DS} = 60V$, $I_D = 70A$
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = 10V$
- Pb-free lead plating; RoHS compliant

Application

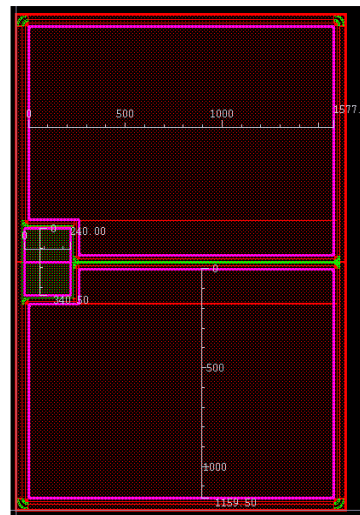
- Synchronous Rectification
- Power management

60V N-Ch Power MOSFET

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(on),typ}$ $V_{GS} = 10V$	9.0	$m\Omega$
I_{D_MAX}	70	A

Physical Characteristics:

Wafer Size (inch)	8
Chip Size with scribe (mm)	1.760x2.570
Wafer Thickness (mil)	6
Top Metal	AlCu
Top Metal Thickness (μm)	4
Back Metal	Ti/Ni/Ag
Scribe Line (μm)	60
Gate Wire recommended	42um Cu or 1mil Al
Source Wires recommended	$\Phi 15mil$ Al*2
Gross Die	6247
Source Pad Dimensions(μm)	1577*1159*2
Gate Pad Dimensions(μm)	240*340



G-Pad:240*340; S-Pad: 1577*1159

Electrical Characteristics at T_j=25°C (unless otherwise specified)

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Drain to Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	60	68		V
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250μA	2	3	4	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =60V, T _j =25°C	-		1	μA
		V _{GS} =0V, V _{DS} =60V, T _j =85°C		-	100	
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±25V, V _{DS} =0V	-		±100	nA
Drain to Source on Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	9.0	14	mΩ
Gate Resistance	R _G	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.2	-	Ω